

I' a first insulation film formed on a rest part of the region, the first insulation film filling spaces between the adjacent conductor patterns, not extending over the etching stopper film, the first insulation film being in contact with side walls of the conductor patterns; and

a sidewall insulation film formed on an inner wall of the contact hole and surrounding the contact hole, the sidewall insulation film covering the side walls of the conductor pattern and the etching stopper film in the contact hole.

36. (Four Times Amended) A semiconductor device comprising:

a base substrate;

a first conducting film formed over the base substrate and including two conductor patterns adjacent to each other;

an etching stopper film covering each upper surface of the two conductor patterns;

I2 a first insulation film formed over the etching stopper film and the base substrate;

a contact hole, located between the two conductor patterns, reaching the base substrate through the first insulation film; and

a sidewall insulation film formed in the contact hole on an inner wall of the first insulation film, each side wall of the two conductor patterns, and each side wall of the etching stopper film, in which

an end of the contact hole is defined by four sides including a first pair of sides which are opposed to each other and a second pair of sides which are opposed to each other,

the first pair of sides is defined by the conductor patterns,

I2 the second pair of sides is defined by the first insulation film,

the sidewall insulation film does not form between the side walls of the conductor patterns
and the first insulation film.
